

MOSFET

600V CoolMOS™ G7 SJ Power Device

The C7 GOLD series (G7) for the first time brings together the benefits of the C7 GOLD CoolMOS™ technology, 4 pin Kelvin Source capability and the improved thermal properties of the TOLL package to enable a possible SMD solution for high current topologies such as PFC up to 3kW

Features

- C7 Gold gives best in class FOM $R_{DS(on)} * E_{oss}$ and $R_{DS(on)} * Q_g$.
- Suitable for hard and soft switching (PFC and high performance LLC)
- C7 Gold technology enables best in class $R_{DS(on)}$ in smallest footprint.
- TOLL package has inbuilt 4th pin Kelvin Source configuration and low parasitic source inductance (~1nH).
- TOLL package is MSL1 compliant, total Pb-free and has easy visual inspection grooved leads.
- TOLL SMD package combined with lead free die attach process enables improved thermal performance R_{th} .

Benefits

- C7 Gold FOM $R_{DS(on)} * Q_g$ is 15% better than previous C7 600V enabling faster switching leading to higher efficiency.
- Increased economies of scale by use in PFC and PWM topologies in the application
- C7 Gold can reach 28mΩ in in TOLL 115mm² footprint, whereas previous BIC C7 600V was 40mΩ in 150mm² D²PAK footprint.
- Reducing parasitic source inductance by Kelvin Source improves efficiency by faster switching and ease of use due to less ringing.
- TOLL package is easy to use and has the highest quality standards.
- Improved thermals enable SMD TOLL package to be used in higher current designs than has been previously possible.

Potential applications

PFC stages and PWM stages (TTF, LLC) for high power/performance SMPS e.g. Computing, Server, Telecom, UPS and Solar.

Product validation

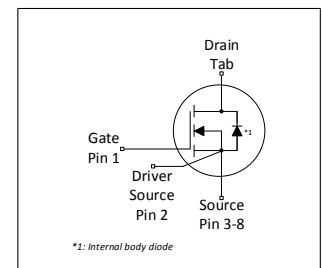
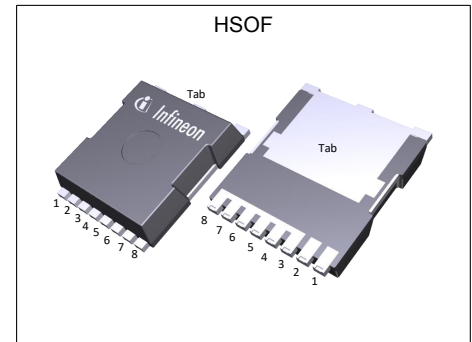
Fully qualified according to JEDEC for Industrial Applications

Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.

Table 1 Key Performance Parameters

| Parameter | Value | Unit |
|---|-------|------|
| $V_{DS} @ T_{j,max}$ | 650 | V |
| $R_{DS(on),max}$ | 150 | mΩ |
| $Q_{g,typ}$ | 23 | nC |
| $I_{D,pulse}$ | 45 | A |
| $I_{D,continuous} @ T_j < 150^{\circ}C$ | 23 | A |
| $E_{oss}@400V$ | 2.74 | μJ |
| Body diode di/dt | 700 | A/μs |

| Type / Ordering Code | Package | Marking | Related Links |
|----------------------|-----------|----------|----------------|
| IPT60R150G7 | PG-HSOF-8 | 60R150G7 | see Appendix A |



RoHS

Table of Contents

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1 Maximum ratings

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Table 2 Maximum ratings

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|--|---------------|--------|------|----------|------------------|---|
| | | Min. | Typ. | Max. | | |
| Continuous drain current ¹⁾ | I_D | - | - | 17 11 | A | $T_C=25^\circ\text{C}$ $T_C=100^\circ\text{C}$ |
| Pulsed drain current ²⁾ | $I_{D,pulse}$ | - | - | 45 | A | $T_C=25^\circ\text{C}$ |
| Avalanche energy, single pulse | E_{AS} | - | - | 53 | mJ | $I_D=3.3\text{A}$; $V_{DD}=50\text{V}$; see table 10 |
| Avalanche energy, repetitive | E_{AR} | - | - | 0.26 | mJ | $I_D=3.3\text{A}$; $V_{DD}=50\text{V}$; see table 10 |
| Avalanche current, single pulse | I_{AS} | - | - | 3.3 | A | - |
| MOSFET dv/dt ruggedness | dv/dt | - | - | 120 | V/ns | $V_{DS}=0\dots400\text{V}$ |
| Gate source voltage (static) | V_{GS} | -20 | - | 20 | V | static; |
| Gate source voltage (dynamic) | V_{GS} | -30 | - | 30 | V | AC ($f>1\text{ Hz}$) |
| Power dissipation | P_{tot} | - | - | 106 | W | $T_C=25^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55 | - | 150 | $^\circ\text{C}$ | - |
| Operating junction temperature | T_j | -55 | - | 150 | $^\circ\text{C}$ | - |
| Mounting torque | - | - | - | n.a. | Ncm | - |
| Continuous diode forward current | I_S | - | - | 17 | A | $T_C=25^\circ\text{C}$ |
| Diode pulse current ²⁾ | $I_{S,pulse}$ | - | - | 45 | A | $T_C=25^\circ\text{C}$ |
| Reverse diode dv/dt ³⁾ | dv/dt | - | - | 25 | V/ns | $V_{DS}=0\dots400\text{V}$, $I_{SD}\leq 5.2\text{A}$, $T_j=25^\circ\text{C}$ see table 8 |
| Maximum diode commutation speed | di/dt | - | - | 700 | A/ μs | $V_{DS}=0\dots400\text{V}$, $I_{SD}\leq 5.2\text{A}$, $T_j=25^\circ\text{C}$ see table 8 |
| Insulation withstand voltage | V_{ISO} | - | - | n.a. | V | V_{rms} , $T_C=25^\circ\text{C}$, $t=1\text{min}$ |

¹⁾ Limited by $T_{j,max}$.

²⁾ Pulse width t_p limited by $T_{j,max}$

³⁾ Identical low side and high side switch

2 Thermal characteristics

Table 3 Thermal characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|---|------------|--------|------|------|------|---|
| | | Min. | Typ. | Max. | | |
| Thermal resistance, junction - case | R_{thJC} | - | - | 1.18 | °C/W | - |
| Thermal resistance, junction - ambient | R_{thJA} | - | - | 62 | °C/W | device on PCB, minimal footprint |
| Thermal resistance, junction - ambient for SMD version | R_{thJA} | - | 35 | 45 | °C/W | Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm ² (one layer, 70µm thickness) copper area for drain connection and cooling. PCB is vertical without air stream cooling. |
| Soldering temperature, wave- & reflow soldering allowed | T_{sold} | - | - | 260 | °C | reflow MSL1 |

3 Electrical characteristics

at $T_j=25^\circ\text{C}$, unless otherwise specified

Table 4 Static characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|----------------------------------|---------------|--------|----------------|-------|---------------|---|
| | | Min. | Typ. | Max. | | |
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | 600 | - | - | V | $V_{GS}=0\text{V}$, $I_D=1\text{mA}$ |
| Gate threshold voltage | $V_{(GS)th}$ | 3 | 3.5 | 4 | V | $V_{DS}=V_{GS}$, $I_D=0.26\text{mA}$ |
| Zero gate voltage drain current | I_{DSS} | - | - | 1 | μA | $V_{DS}=600$, $V_{GS}=0\text{V}$, $T_j=25^\circ\text{C}$ $V_{DS}=600$, $V_{GS}=0\text{V}$, $T_j=150^\circ\text{C}$ |
| Gate-source leakage current | I_{GSS} | - | - | 100 | nA | $V_{GS}=20\text{V}$, $V_{DS}=0\text{V}$ |
| Drain-source on-state resistance | $R_{DS(on)}$ | - | 0.129 0.323 | 0.150 | Ω | $V_{GS}=10\text{V}$, $I_D=5.3\text{A}$, $T_j=25^\circ\text{C}$ $V_{GS}=10\text{V}$, $I_D=5.3\text{A}$, $T_j=150^\circ\text{C}$ |
| Gate resistance | R_G | - | 0.8 | - | Ω | $f=1\text{MHz}$, open drain |

Table 5 Dynamic characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|--|--------------|--------|------|------|------|--|
| | | Min. | Typ. | Max. | | |
| Input capacitance | C_{iss} | - | 902 | - | pF | $V_{GS}=0\text{V}$, $V_{DS}=400\text{V}$, $f=250\text{kHz}$ |
| Output capacitance | C_{oss} | - | 19 | - | pF | $V_{GS}=0\text{V}$, $V_{DS}=400\text{V}$, $f=250\text{kHz}$ |
| Effective output capacitance, energy related ¹⁾ | $C_{o(er)}$ | - | 34 | - | pF | $V_{GS}=0\text{V}$, $V_{DS}=0\dots400\text{V}$ |
| Effective output capacitance, time related ²⁾ | $C_{o(tr)}$ | - | 350 | - | pF | $I_D=\text{constant}$, $V_{GS}=0\text{V}$, $V_{DS}=0\dots400\text{V}$ |
| Turn-on delay time | $t_{d(on)}$ | - | 17 | - | ns | $V_{DD}=400\text{V}$, $V_{GS}=13\text{V}$, $I_D=5.3\text{A}$, $R_G=10\Omega$; see table 9 |
| Rise time | t_r | - | 5 | - | ns | $V_{DD}=400\text{V}$, $V_{GS}=13\text{V}$, $I_D=5.3\text{A}$, $R_G=10\Omega$; see table 9 |
| Turn-off delay time | $t_{d(off)}$ | - | 56 | - | ns | $V_{DD}=400\text{V}$, $V_{GS}=13\text{V}$, $I_D=5.3\text{A}$, $R_G=10\Omega$; see table 9 |
| Fall time | t_f | - | 6 | - | ns | $V_{DD}=400\text{V}$, $V_{GS}=13\text{V}$, $I_D=5.3\text{A}$, $R_G=10\Omega$; see table 9 |

Table 6 Gate charge characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|-----------------------|----------------------|--------|------|------|------|---|
| | | Min. | Typ. | Max. | | |
| Gate to source charge | Q_{GS} | - | 5 | - | nC | $V_{DD}=400\text{V}$, $I_D=5.3\text{A}$, $V_{GS}=0$ to 10V |
| Gate to drain charge | Q_{gd} | - | 8 | - | nC | $V_{DD}=400\text{V}$, $I_D=5.3\text{A}$, $V_{GS}=0$ to 10V |
| Gate charge total | Q_g | - | 23 | - | nC | $V_{DD}=400\text{V}$, $I_D=5.3\text{A}$, $V_{GS}=0$ to 10V |
| Gate plateau voltage | V_{plateau} | - | 5.0 | - | V | $V_{DD}=400\text{V}$, $I_D=5.3\text{A}$, $V_{GS}=0$ to 10V |

¹⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 400V

²⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 400V

Table 7 Reverse diode characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|-------------------------------|-----------|--------|------|------|---------|---|
| | | Min. | Typ. | Max. | | |
| Diode forward voltage | V_{SD} | - | 0.8 | - | V | $V_{GS}=0V, I_F=5.3A, T_j=25^{\circ}C$ |
| Reverse recovery time | t_{rr} | - | 245 | - | ns | $V_R=400V, I_F=5.3A, di_F/dt=100A/\mu s$; see table 8 |
| Reverse recovery charge | Q_{rr} | - | 2.2 | - | μC | $V_R=400V, I_F=5.3A, di_F/dt=100A/\mu s$; see table 8 |
| Peak reverse recovery current | I_{rrm} | - | 19 | - | A | $V_R=400V, I_F=5.3A, di_F/dt=100A/\mu s$; see table 8 |

4 Electrical characteristics diagrams

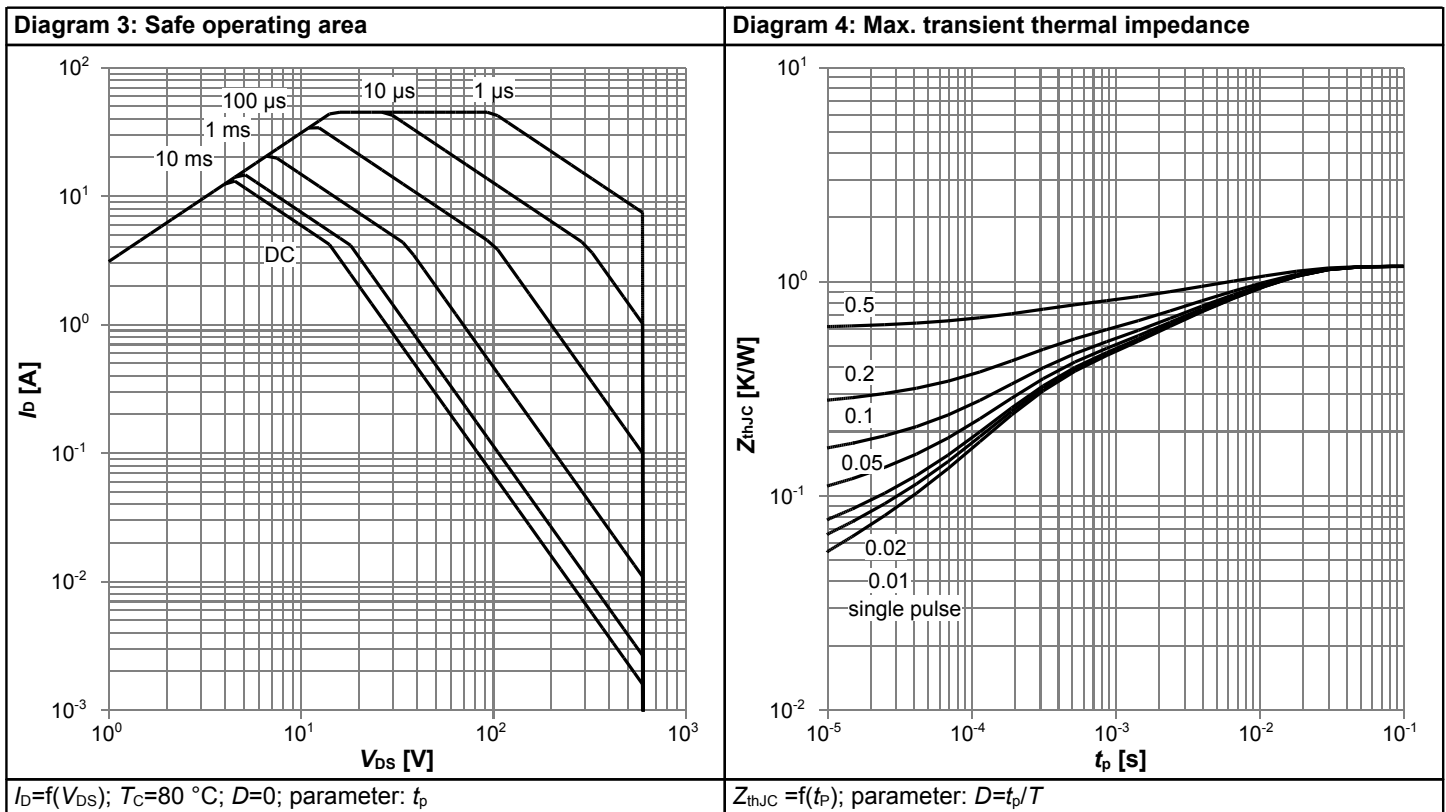
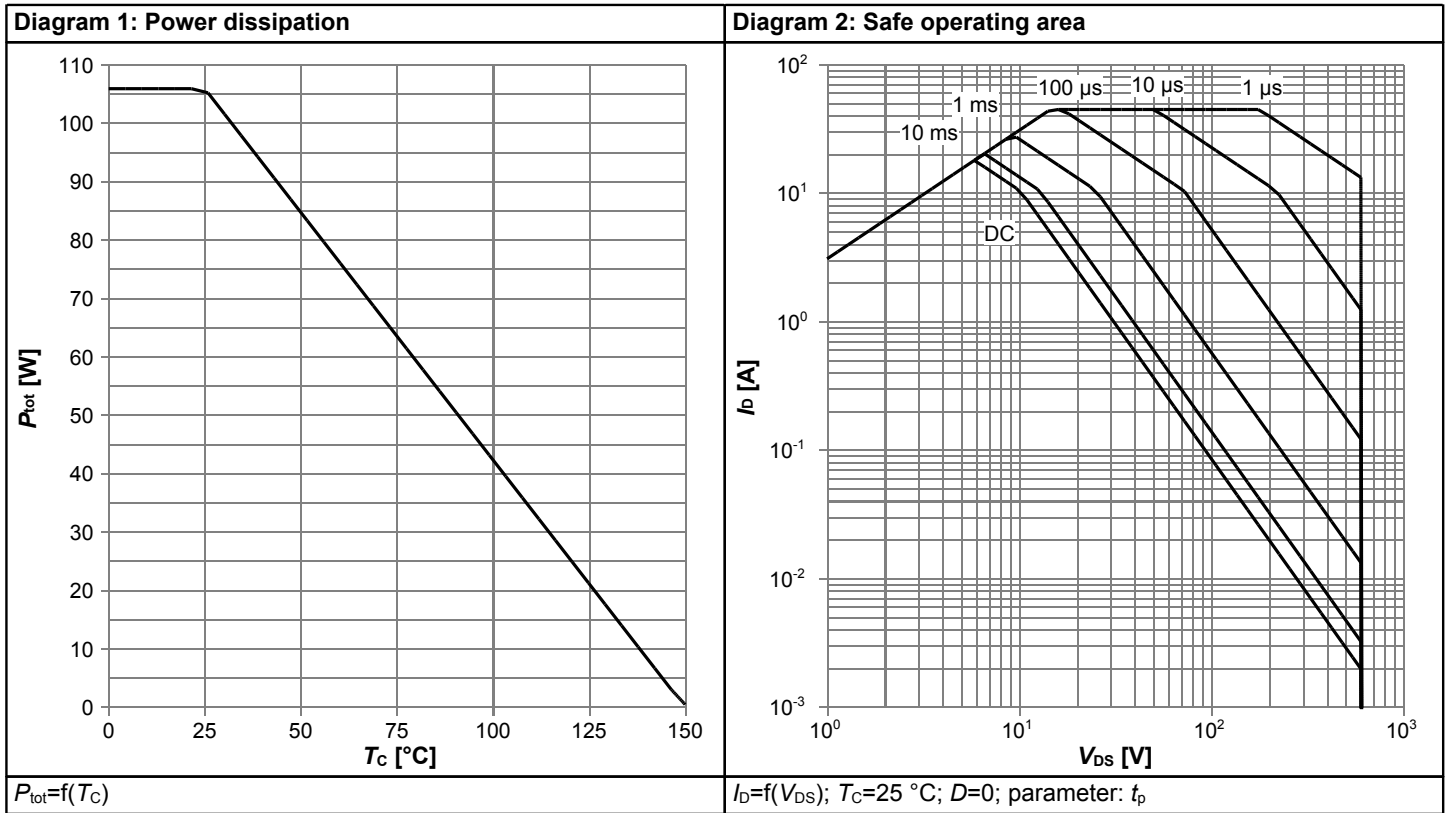
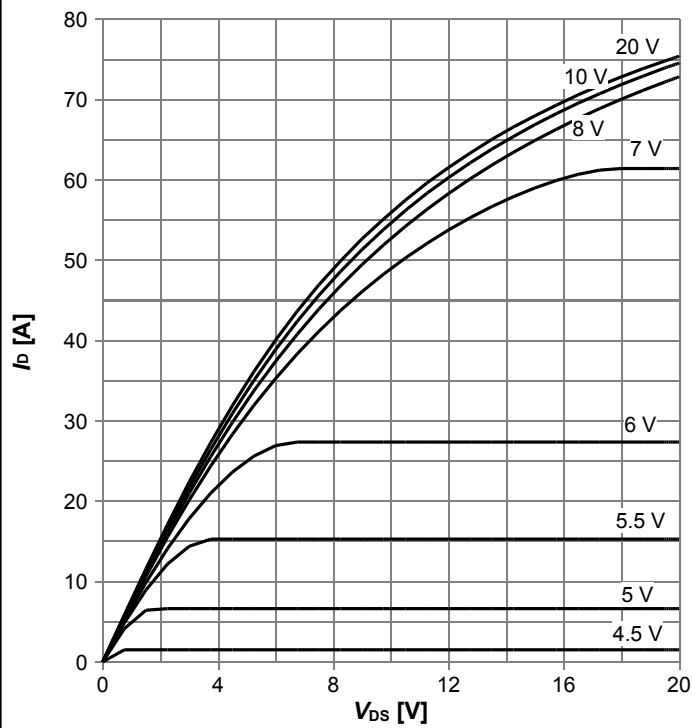
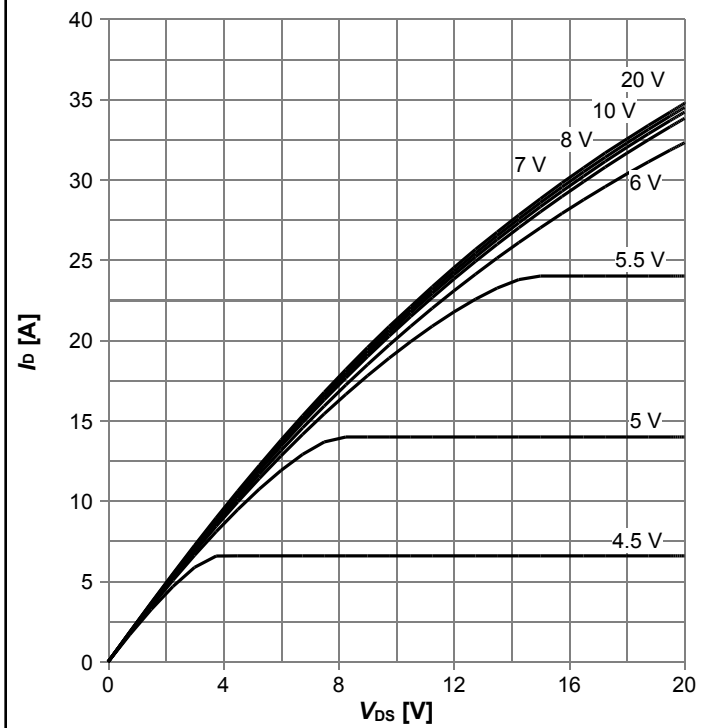


Diagram 5: Typ. output characteristics



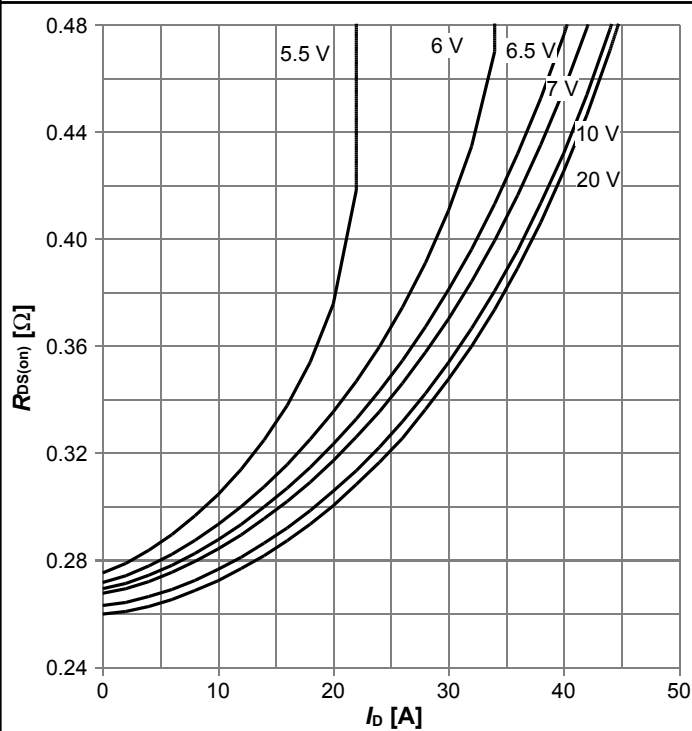
$I_D=f(V_{DS})$; $T_j=25^\circ\text{C}$; parameter: V_{GS}

Diagram 6: Typ. output characteristics



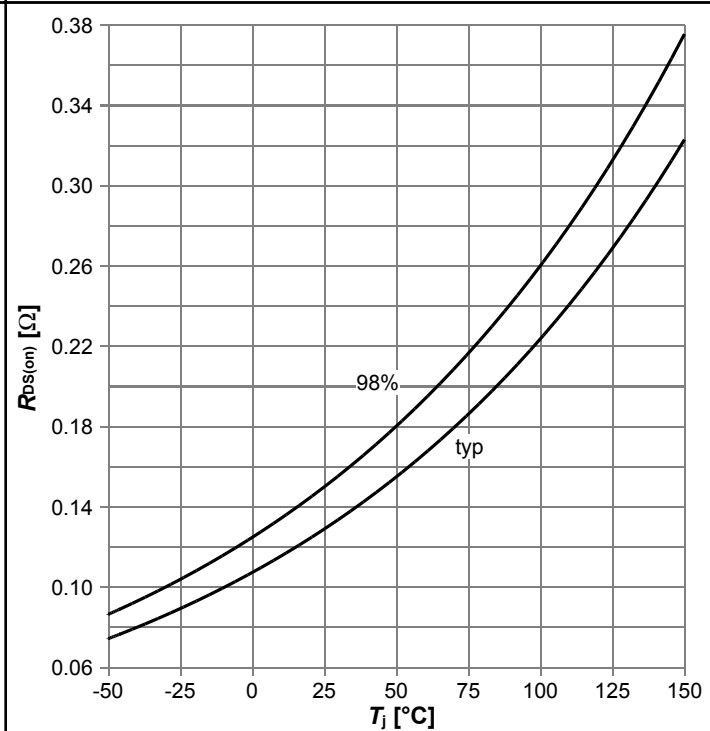
$I_D=f(V_{DS})$; $T_j=125^\circ\text{C}$; parameter: V_{GS}

Diagram 7: Typ. drain-source on-state resistance



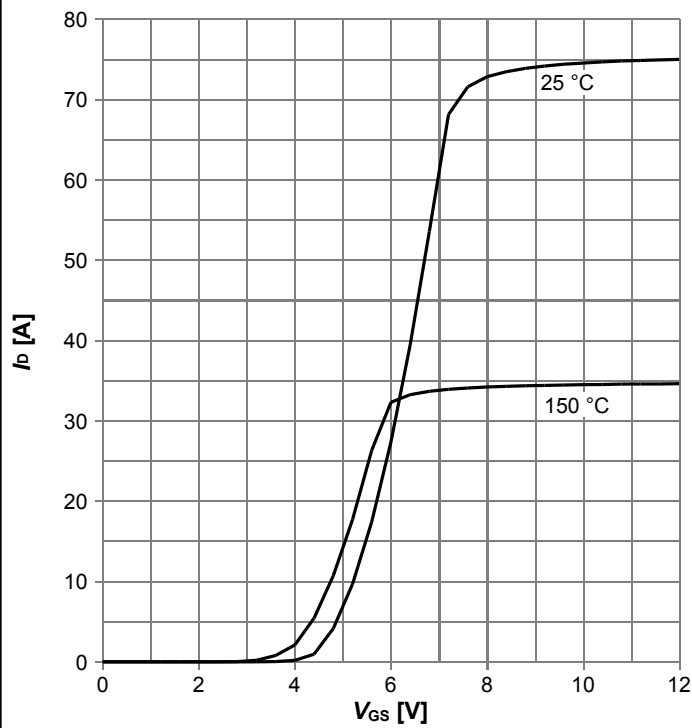
$R_{DS(on)}=f(I_D)$; $T_j=125^\circ\text{C}$; parameter: V_{GS}

Diagram 8: Drain-source on-state resistance



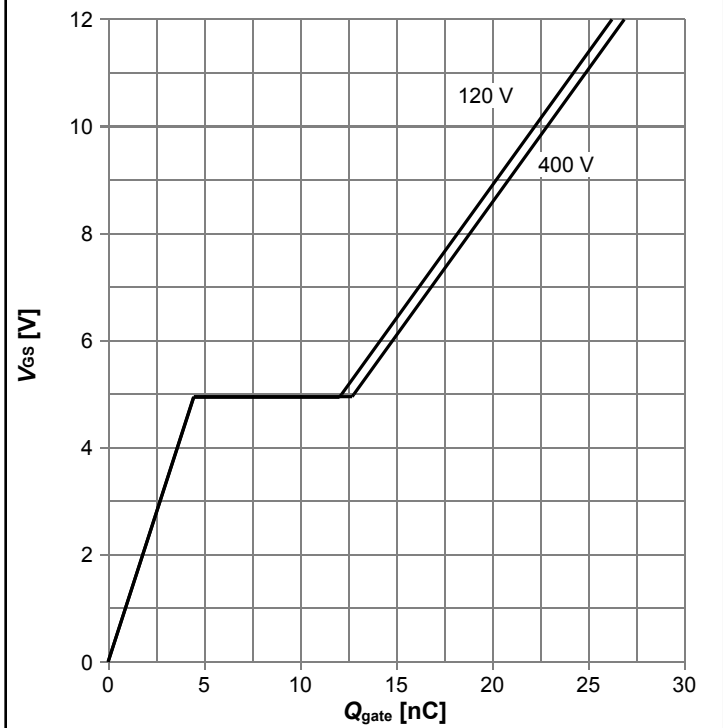
$R_{DS(on)}=f(T_j)$; $I_D=5.3\text{ A}$; $V_{GS}=10\text{ V}$

Diagram 9: Typ. transfer characteristics



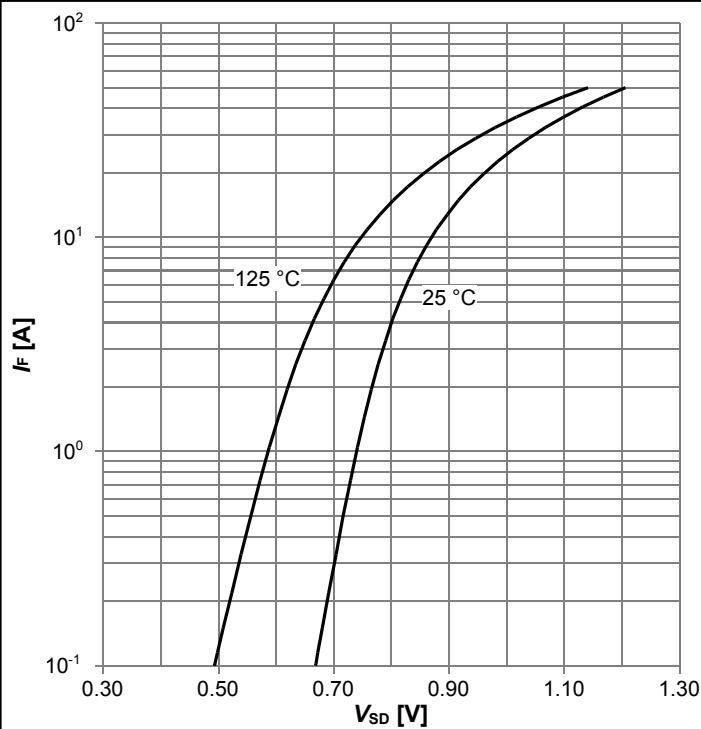
$I_D = f(V_{GS}); V_{DS} = 20V; \text{parameter: } T_j$

Diagram 10: Typ. gate charge



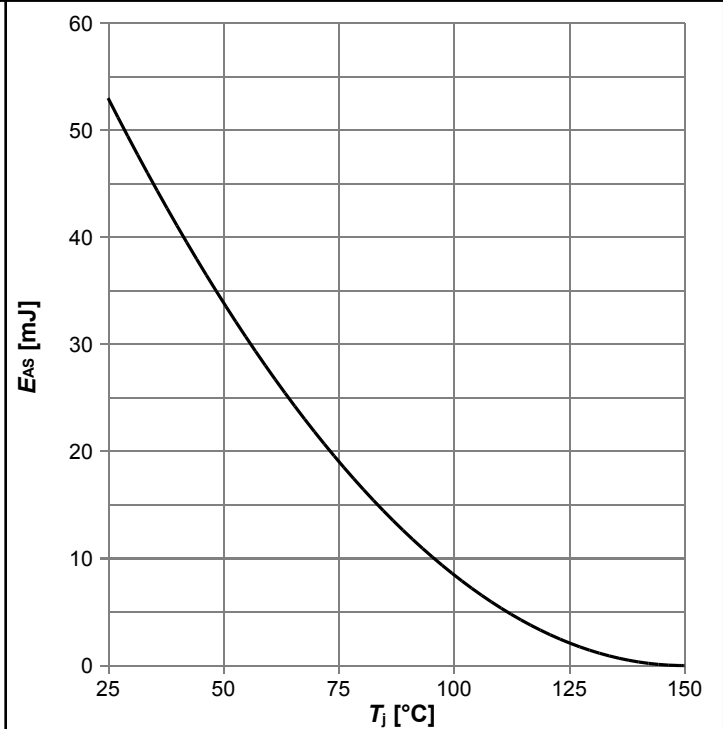
$V_{GS} = f(Q_{gate}); I_D = 5.3 \text{ A pulsed}; \text{parameter: } V_{DD}$

Diagram 11: Forward characteristics of reverse diode



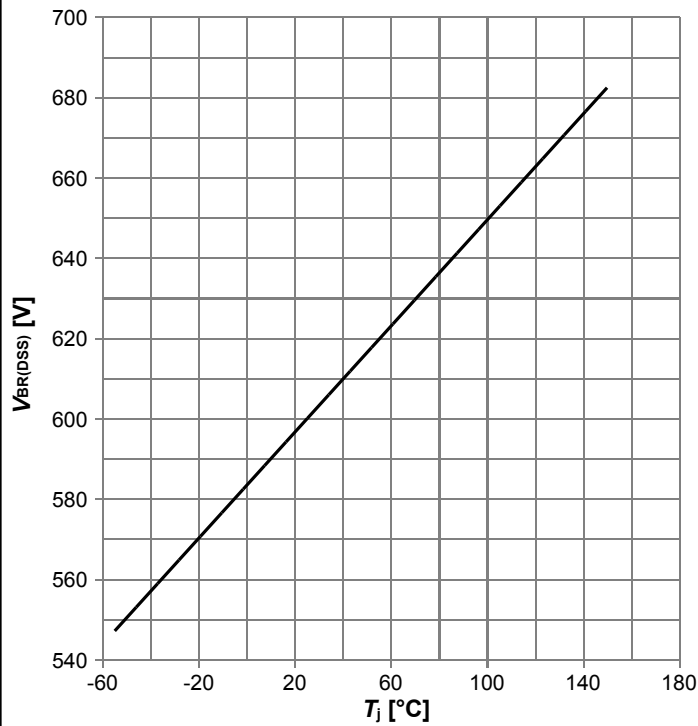
$I_F = f(V_{SD}); \text{parameter: } T_j$

Diagram 12: Avalanche energy



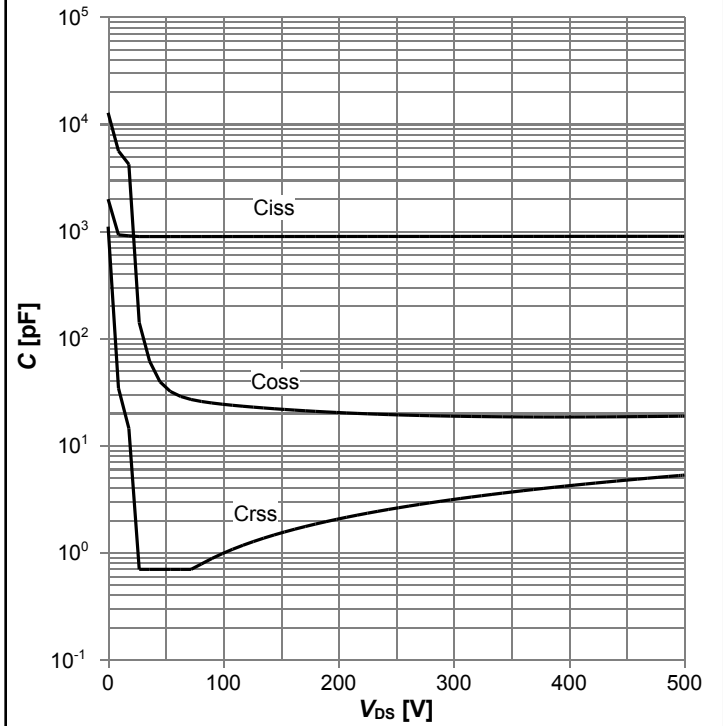
$E_{AS} = f(T_j); I_D = 3.3 \text{ A}; V_{DD} = 50 \text{ V}$

Diagram 13: Drain-source breakdown voltage



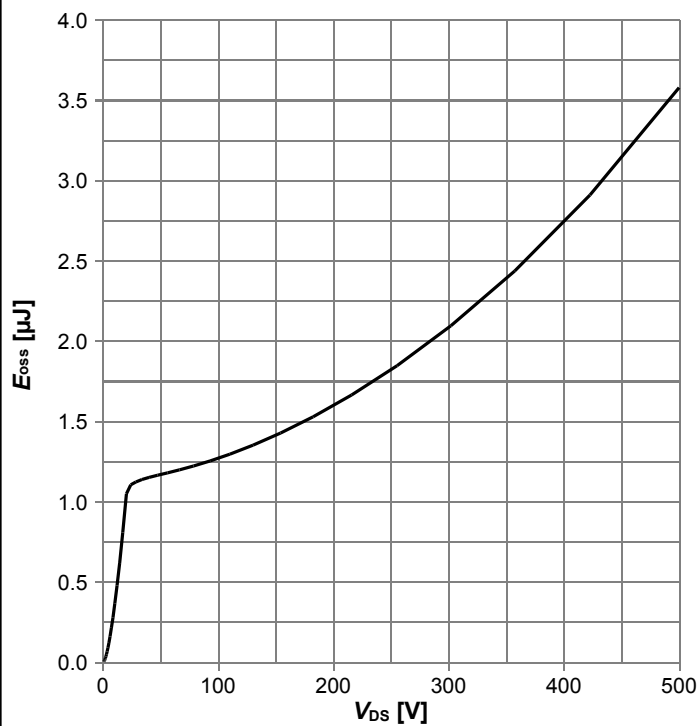
$V_{BR(DSS)}=f(T_j); I_D=1\text{ mA}$

Diagram 14: Typ. capacitances



$C=f(V_{DS}); V_{GS}=0\text{ V}; f=250\text{ kHz}$

Diagram 15: Typ. Coss stored energy



$E_{oss}=f(V_{DS})$

5 Test Circuits

Table 8 Diode characteristics



Table 9 Switching times (ss)

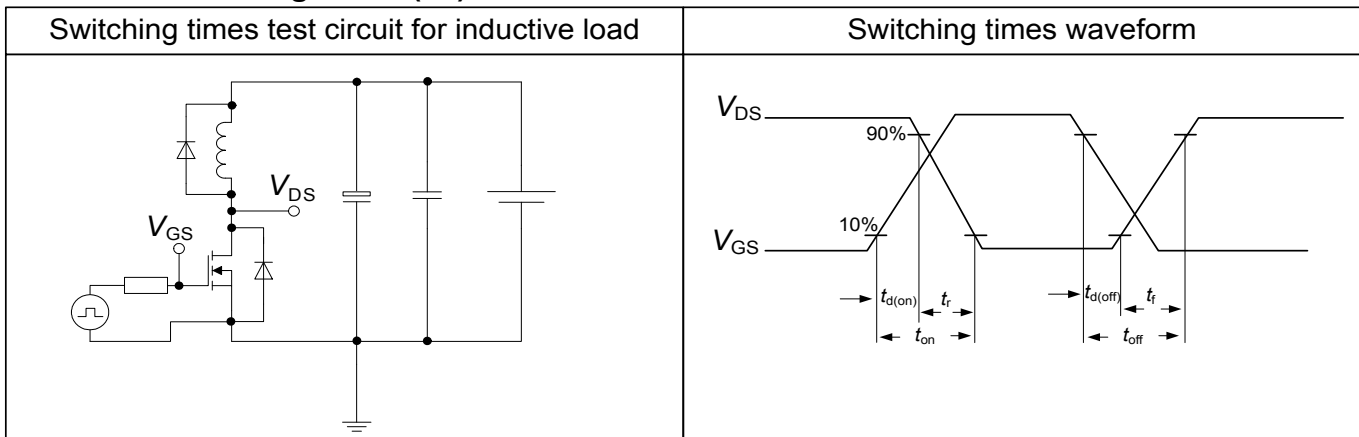
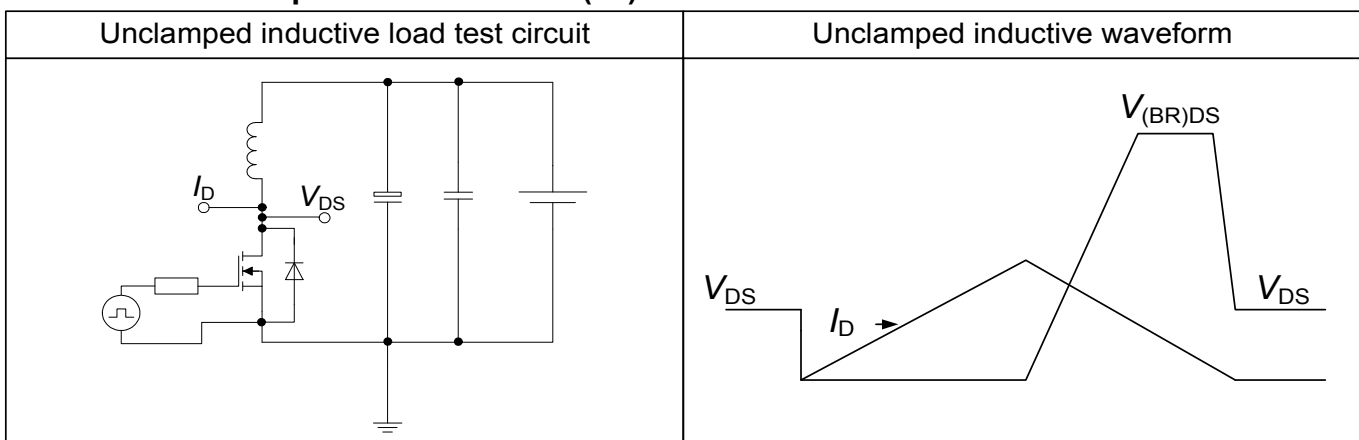


Table 10 Unclamped inductive load (ss)



6 Package Outlines

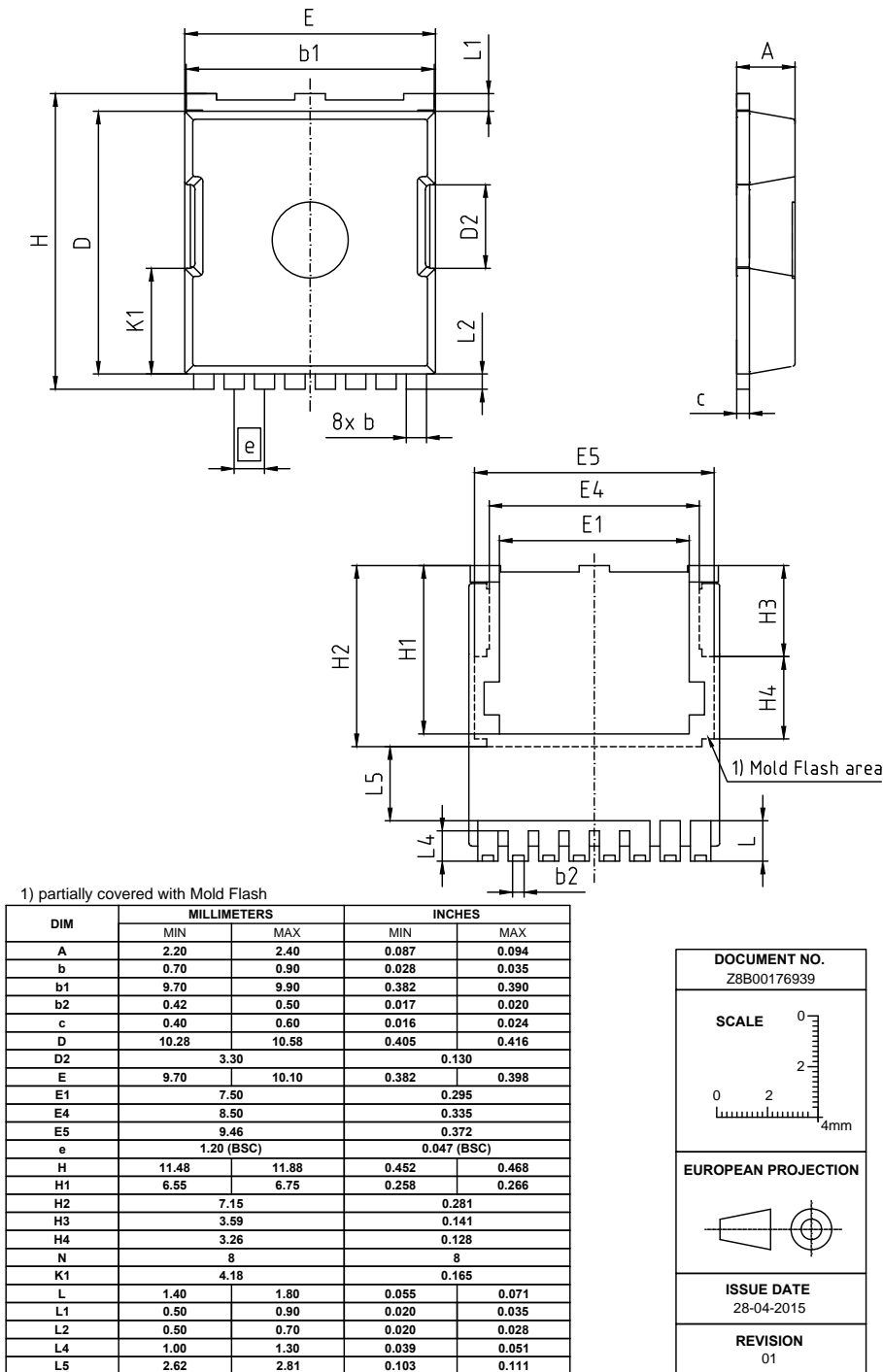


Figure 1 Outline PG-HSOF-8, dimensions in mm/inches

7 Appendix A

Table 11 Related Links

- IFX CoolMOS™ G7 Webpage: www.infineon.com
- IFX CoolMOS™ G7 application note: www.infineon.com
- IFX CoolMOS™ G7 simulation model: www.infineon.com
- IFX Design tools: www.infineon.com

Revision History

IPT60R150G7

Revision: 2020-10-28, Rev. 2.1

Previous Revision

| Revision | Date | Subjects (major changes since last revision) |
|----------|------------|--|
| 2.0 | 2016-12-15 | Release of final version |
| 2.1 | 2020-10-28 | Content update diagram 2,3,4,7,8 and format update |

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